



**THE DATASHEET OF
MOC3081M**



6-Pin DIP Zero-Cross Triac Driver Optocoupler (800 V Peak)

MOC3081M, MOC3082M, MOC3083M

Description

The MOC3081M, MOC3082M and MOC3083M devices consist of a GaAs infrared emitting diode optically coupled to a monolithic silicon detector performing the function of a zero voltage crossing bilateral triac driver.

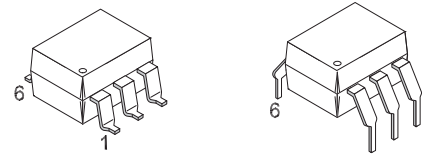
They are designed for use with a discrete power triac in the interface of logic systems to equipment powered from 240 VAC lines, such as solid-state relays, industrial controls, motors, solenoids and consumer appliances, etc.

Features

- Simplifies Logic Control of 240 VAC Power
- Zero Voltage Crossing to Minimize Conducted and Radiated Line Noise
- 800 V Peak Blocking Voltage
- Superior Static dv/dt
 - ◆ 1500 V/μs Typical, 600 V/μs Guaranteed
- Safety and Regulatory Approvals
 - ◆ UL1577, 4,170 VAC_{RMS} for 1 Minute
 - ◆ DIN EN/IEC60747-5-5
- These are Pb-Free Devices

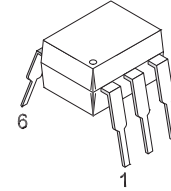
Applications

- Solenoid/Valve Controls
- Lighting Controls
- Static Power Switches
- AC Motor Starters
- Temperature Controls
- E.M. Contactors
- AC Motor Drives
- Solid State Relays

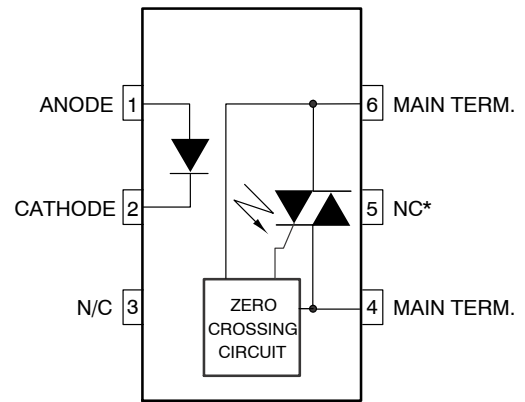


PDIP6 8.51x6.35, 2.54P
CASE 646BY

PDIP6 8.51x6.35, 2.54P
CASE 646BZ



PDIP6 8.51x6.35, 2.54P
CASE 646BX



*DO NOT CONNECT
(TRIAC SUBSTRATE)

Figure 1. Schematic

ORDERING INFORMATION

See detailed ordering and shipping information on page 9 of this data sheet.

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SAFETY AND INSULATION RATINGS

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

| Parameter | | Characteristics |
|---|------------------------|-----------------|
| Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated Mains Voltage | < 150 V _{RMS} | I-IV |
| | < 300 V _{RMS} | I-IV |
| Climatic Classification | | 40/85/21 |
| Pollution Degree (DIN VDE 0110/1.89) | | 2 |
| Comparative Tracking Index | | 175 |

| Symbol | Parameter | Value | Unit |
|-------------------|--|-------------------|-------------------|
| V _{PR} | Input-to-Output Test Voltage, Method A, V _{IORM} × 1.6 = V _{PR} , Type and Sample Test with t _m = 10 s, Partial Discharge < 5 pC | 1360 | V _{peak} |
| | Input-to-Output Test Voltage, Method B, V _{IORM} × 1.875 = V _{PR} , 100% Production Test with t _m = 1 s, Partial Discharge < 5 pC | 1594 | V _{peak} |
| V _{IORM} | Maximum Working Insulation Voltage | 850 | V _{peak} |
| V _{IOTM} | Highest Allowable Over-Voltage | 6000 | V _{peak} |
| | External Creepage | ≥ 7 | mm |
| | External Clearance | ≥ 7 | mm |
| | External Clearance (for Option TV, 0.4" Lead Spacing) | ≥ 10 | mm |
| DTI | Distance Through Insulation (Insulation Thickness) | ≥ 0.5 | mm |
| R _{IO} | Insulation Resistance at T _S , V _{IO} = 500 V | > 10 ⁹ | Ω |

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ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

| Symbol | Parameters | Value | Unit |
|--------|------------|-------|------|
|--------|------------|-------|------|

Total Device

| | | | |
|------------------|--|--------------------|-------|
| T _{STG} | Storage Temperature | -40 to 125 | °C |
| T _{OPR} | Operating Temperature | -40 to 85 | °C |
| T _J | Junction Temperature Range | -40 to 100 | °C |
| T _{SOL} | Lead Solder Temperature | 260 for 10 seconds | °C |
| P _D | Total Device Power Dissipation at 25°C Ambient | 250 | mW |
| | Derate Above 25°C | 2.94 | mW/°C |

Emitter

| | | | |
|----------------|---|------|-------|
| I _F | Continuous Forward Current | 60 | mA |
| V _R | Reverse Voltage | 6 | V |
| P _D | Total Power Dissipation at 25°C Ambient | 120 | mW |
| | Derate Above 25°C | 1.41 | mW/°C |

Detector

| | | | |
|------------------|---|------|-------|
| V _{DRM} | Off-State Output Terminal Voltage | 800 | V |
| I _{TSM} | Peak Non-Repetitive Surge Current (Single Cycle 60 Hz Sine Wave) | 1 | A |
| P _D | Total Power Dissipation at 25°C Ambient | 150 | mW |
| | Derate Above 25°C | 1.76 | mW/°C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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ELECTRICAL CHARACTERISTICS

$T_A = 25^\circ\text{C}$ unless otherwise specified

INDIVIDUAL COMPONENT CHARACTERISTICS

| Symbol | Parameters | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------|--|--|------|-------|------|------------------|
| Emitter | | | | | | |
| V_F | Input Forward Voltage | $I_F = 30\text{ mA}$ | | 1.3 | 1.5 | V |
| I_R | Reverse Leakage Current | $V_R = 6\text{ V}$ | | 0.005 | 100 | μA |
| Detector | | | | | | |
| I_{DRM1} | Peak Blocking Current, Either Direction | $V_{DRM} = 800\text{ V}$, $I_F = 0^{(1)}$ | | 10 | 500 | nA |
| dv/dt | Critical Rate of Rise of Off-State Voltage | $I_F = 0$ (Figure 10) ⁽²⁾ | 600 | 1500 | | V/ μs |

1. Test voltage must be applied within dv/dt rating.
2. This is static dv/dt. See Figure 11 for test circuit. Commutating dv/dt is a function of the load-driving thyristor(s) only.

TRANSFER CHARACTERISTICS

| Symbol | DC Characteristics | Test Conditions | Device | Min. | Typ. | Max. | Unit |
|----------|---|--|----------|------|------|------|---------------|
| I_{FT} | LED Trigger Current (Rated I_{FT}) | Main Terminal Voltage = $3\text{ V}^{(3)}$ | MOC3081M | | | 15 | mA |
| | | | MOC3082M | | | 10 | |
| | | | MOC3083M | | | 5 | |
| V_{TM} | Peak On-State Voltage, Either Direction | $I_{TM} = 100\text{ mA peak}$, $I_F = \text{rated } I_{FT}$ | All | | 1.8 | 3.0 | V |
| I_H | Holding Current, Either Direction | | All | | 500 | | μA |

3. All devices are guaranteed to trigger at an I_F value less than or equal to max I_{FT} . Therefore, recommended operating I_F lies between max I_{FT} (15 mA for MOC3081M, 10 mA for MOC3082M, 5 mA for MOC3083M) and absolute maximum I_F (60 mA).

ZERO CROSSING CHARACTERISTICS

| Symbol | Parameters | Test Conditions | Min. | Typ. | Max. | Unit |
|------------|---|---|------|------|------|------|
| V_{INH} | Inhibit Voltage (MT1–MT2 voltage above which device will not trigger) | $I_F = \text{Rated } I_{FT}$ | | 12 | 20 | V |
| I_{DRM2} | Leakage in Inhibited State | $I_F = \text{Rated } I_{FT}$, $V_{DRM} = 800\text{ V}$, off-state | | | 2 | mA |

ISOLATION CHARACTERISTICS

| Symbol | Parameters | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------|----------------------------------|--|------|-----------|------|----------------|
| V_{ISO} | Isolation Voltage ⁽⁴⁾ | $f = 60\text{ Hz}$, $t = 1\text{ Minute}$ | 4170 | | | $V_{AC_{RMS}}$ |
| R_{ISO} | Isolation Resistance | $V_{I-O} = 500\text{ V}_{DC}$ | | 10^{11} | | Ω |
| C_{ISO} | Isolation Capacitance | $V = 0\text{ V}$, $f = 1\text{ MHz}$ | | 0.2 | | pF |

4. Isolation voltage, V_{ISO} , is an internal device dielectric breakdown rating. For this test, pins 1 and 2 are common, and pins 4, 5 and 6 are common.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CURVES

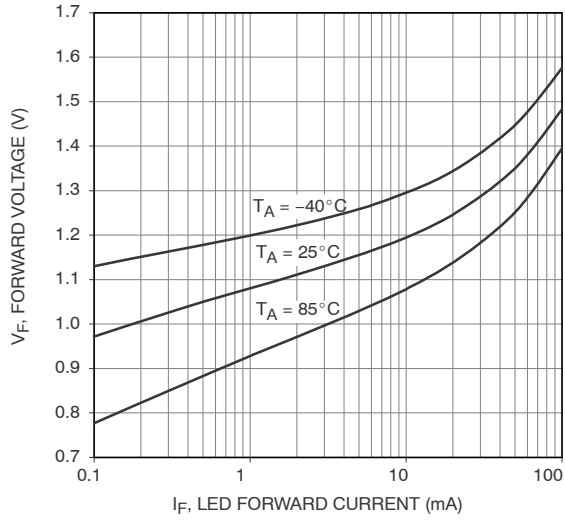


Figure 2. LED Forward Voltage vs. Forward Current

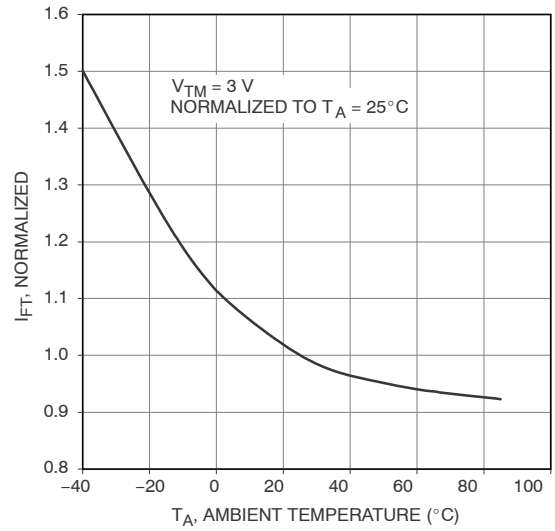


Figure 3. Trigger Current vs. Temperature

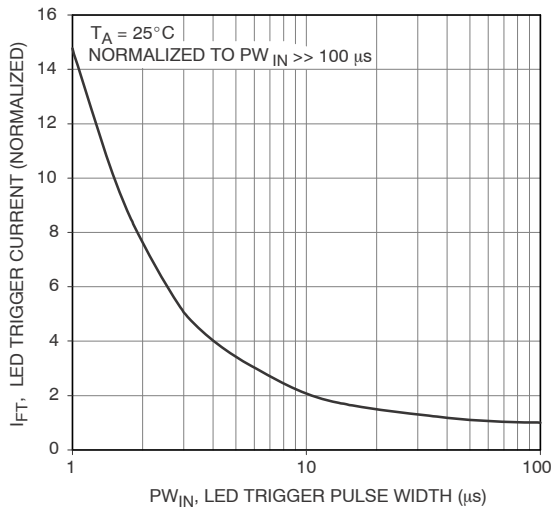


Figure 4. LED Current Required to Trigger vs. LED Pulse Width

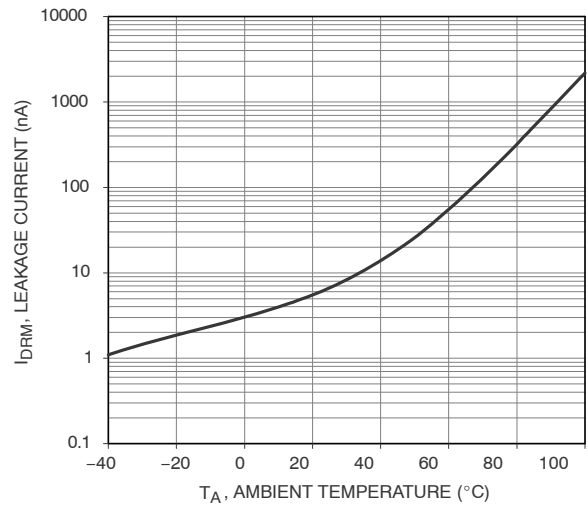


Figure 5. Leakage Current, I_{DRM} vs. Temperature

MOC3081M, MOC3082M, MOC3083M

TYPICAL PERFORMANCE CURVES (CONTINUED)

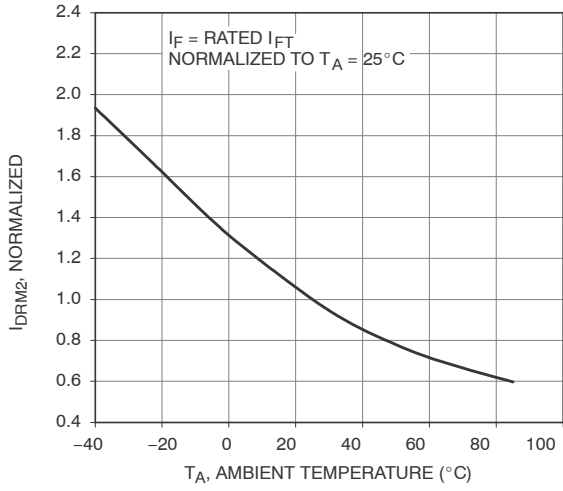


Figure 6. I_{DRM2} , Leakage in Inhibit State vs. Temperature

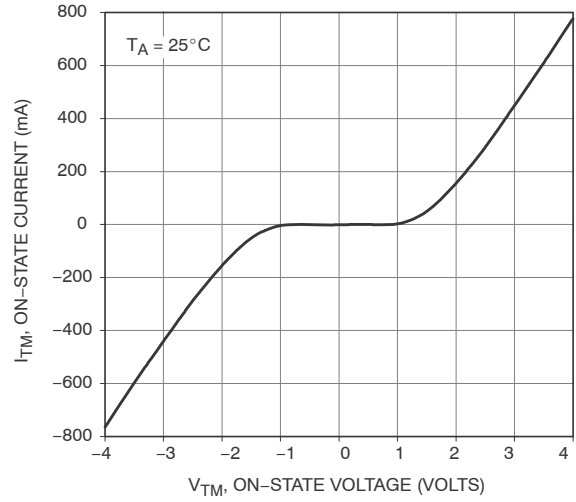


Figure 7. On-State Characteristics

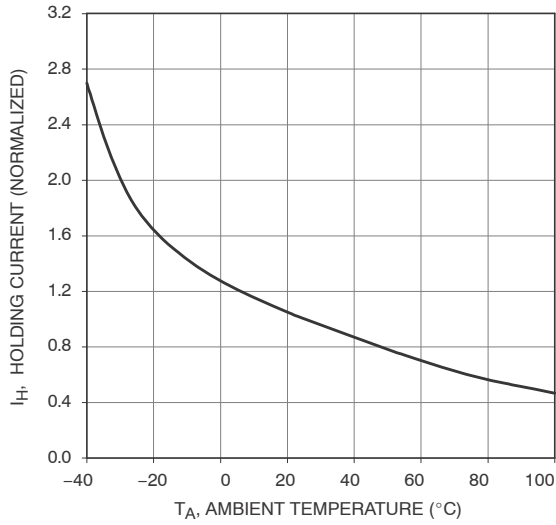


Figure 8. I_H , Holding Current vs. Temperature

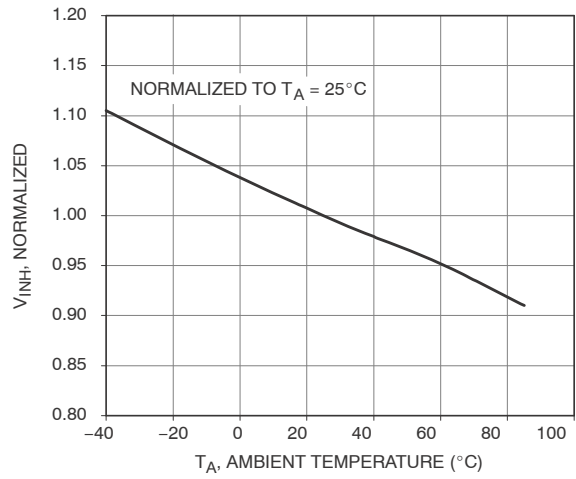
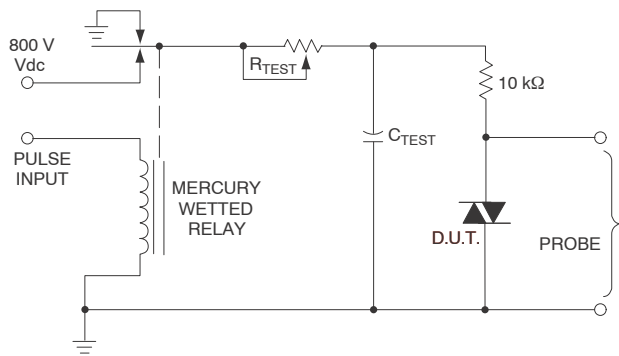


Figure 9. Inhibit Voltage vs. Temperature

MOC3081M, MOC3082M, MOC3083M



1. The mercury wetted relay provides a high speed repeated pulse to the D.U.T.
2. 100x scope probes are used, to allow high speeds and voltages.
3. The worst-case condition for static dv/dt is established by triggering the D.U.T. with a normal LED input current, then removing the current. The variable R_{TEST} allows the dv/dt to be gradually increased until the D.U.T. continues to trigger in response to the applied voltage pulse, even after the LED current has been removed. The dv/dt is then decreased until the D.U.T. stops triggering. τ_{RC} is measured at this point and recorded.

Figure 10. Static dv/dt Test Circuit

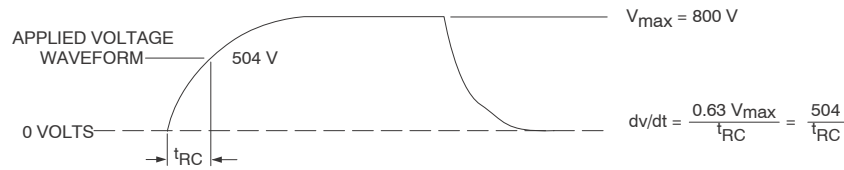
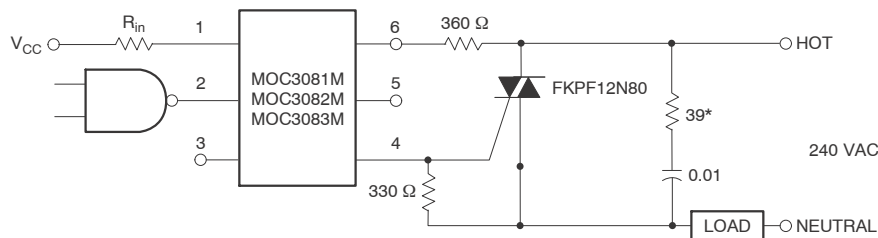


Figure 11. Static dv/dt Test Waveform

Typical circuit for use when hot line switching is required. In this circuit the “hot” side of the line is switched and the load connected to the cold or neutral side. The load may be connected to either the neutral or hot line.

R_{IN} is calculated so that I_F is equal to the rated I_{FT} of the part, 15 mA for the MOC3081M, 10 mA for the

MOC3082M, and 5 mA for the MOC3083M. The 39 Ω resistor and 0.01 μ F capacitor are for snubbing of the triac and may or may not be necessary depending upon the particular triac and load use.



* For highly inductive loads (power factor < 0.5), change this value to 360 Ω .

Figure 12. Hot-Line Switching Application Circuit

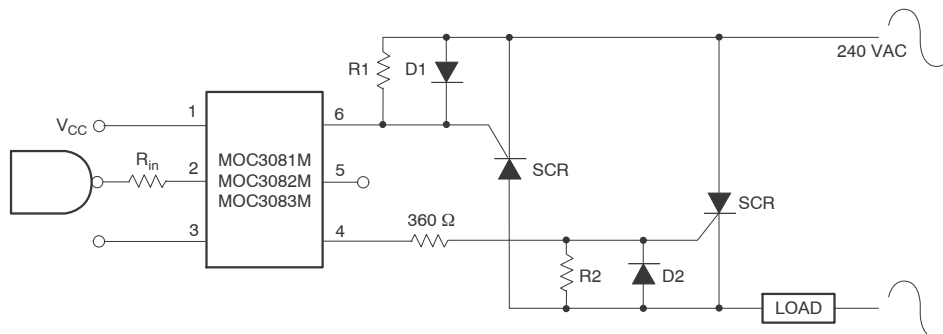


Figure 13. Inverse-Parallel SCR Driver Circuit

Suggested method of firing two, back-to-back SCR's with an ON Semiconductor triac driver. Diodes can be 1N4001; resistors, R1 and R2, are optional 330 Ω .

NOTE: This optoisolator should not be used to drive a load directly. It is intended to be a trigger device only.

Reflow Profile

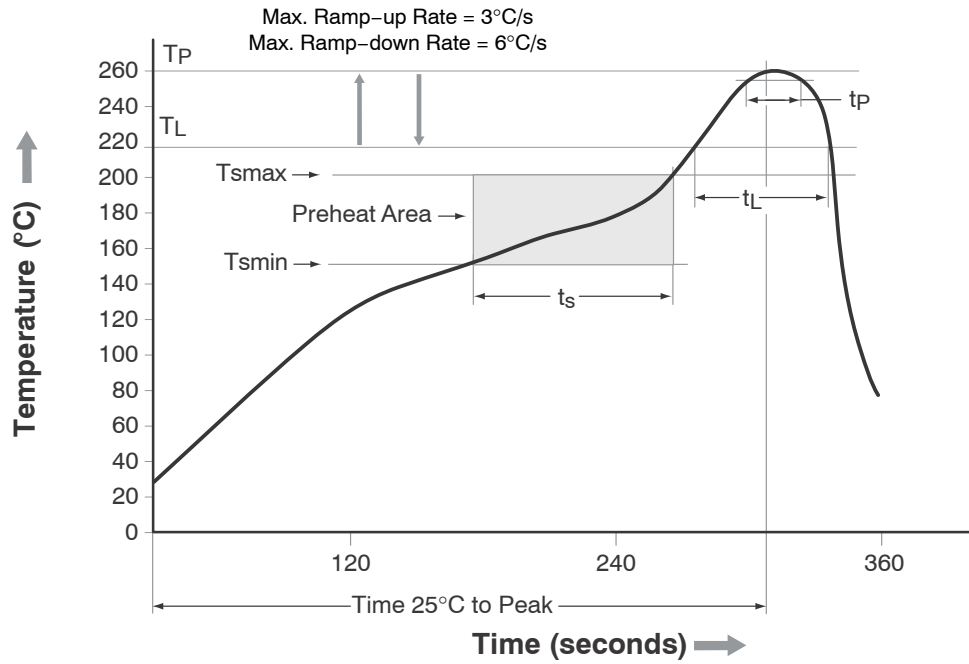


Figure 14. Reflow Profile

| Profile Feature | Pb-Free Assembly Profile |
|---|---------------------------|
| Temperature Minimum (T _{min}) | 150°C |
| Temperature Maximum (T _{max}) | 200°C |
| Time (t _s) from (T _{min} to T _{max}) | 60 seconds to 120 seconds |
| Ramp-up Rate (T _L to T _P) | 3°C/second maximum |
| Liquidous Temperature (T _L) | 217°C |
| Time (t _L) Maintained Above (T _L) | 60 seconds to 150 seconds |
| Peak Body Package Temperature | 260°C +0°C / -5°C |
| Time (t _P) within 5°C of 260°C | 30 seconds |
| Ramp-down Rate (T _P to T _L) | 6°C/second maximum |
| Time 25°C to Peak Temperature | 8 minutes maximum |

MOC3081M, MOC3082M, MOC3083M

ORDERING INFORMATION

| Part Number | Package | Shipping |
|--------------|--|--------------------------|
| MOC3081M | DIP 6-Pin | 50 Units / Tube |
| MOC3081SM | SMT 6-Pin (Lead Bend) | 50 Units / Tube |
| MOC3081SR2M | SMT 6-Pin (Lead Bend) | 1000 Units / Tape & Reel |
| MOC3081VM | DIP 6-Pin, DIN EN/IEC60747-5-5 Option | 50 Units / Tube |
| MOC3081SVM | SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option | 50 Units / Tube |
| MOC3081SR2VM | SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option | 1000 Units / Tape & Reel |
| MOC3081TVM | DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option | 50 Units / Tube |

NOTE: The product orderable part number system listed in this table also applies to the MOC3011M, MOC3012M, MOC3020M, MOC3021M, MOC3022M, and MOC3083M product families.

MARKING INFORMATION

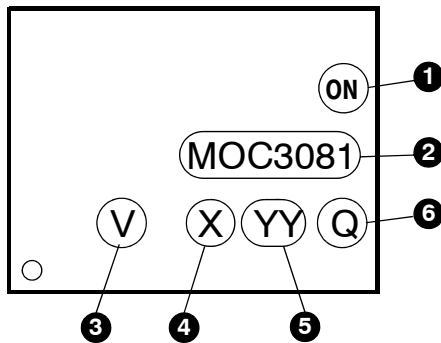


Figure 15. Top Mark

| Top Mark Definitions | |
|----------------------|---|
| 1 | ON Semiconductor Logo |
| 2 | Device Number |
| 3 | DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option) |
| 4 | One-Digit Year Code, e.g., '5' |
| 5 | Two-Digit Work Week, Ranging from '01' to '53' |
| 6 | Assembly Package Code |

MECHANICAL CASE OUTLINE

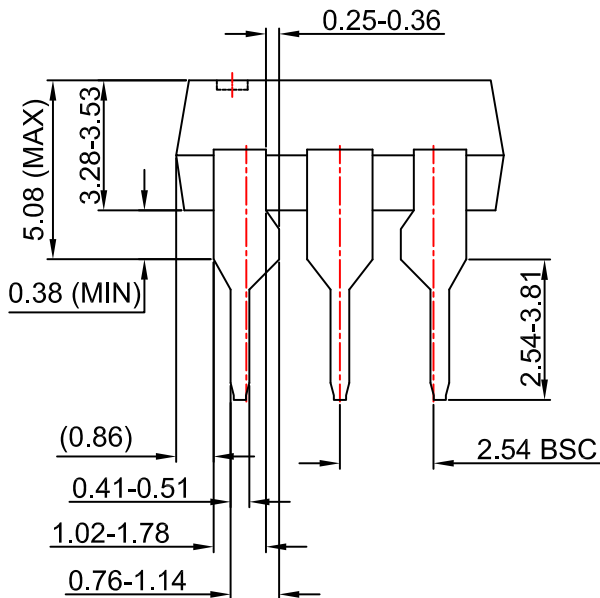
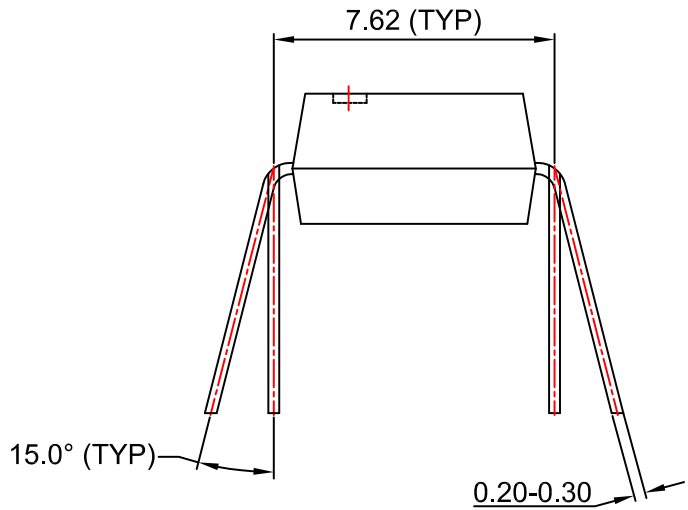
PACKAGE DIMENSIONS

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CASE 646BX
ISSUE O

DATE 31 JUL 2016



NOTES:

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MECHANICAL CASE OUTLINE

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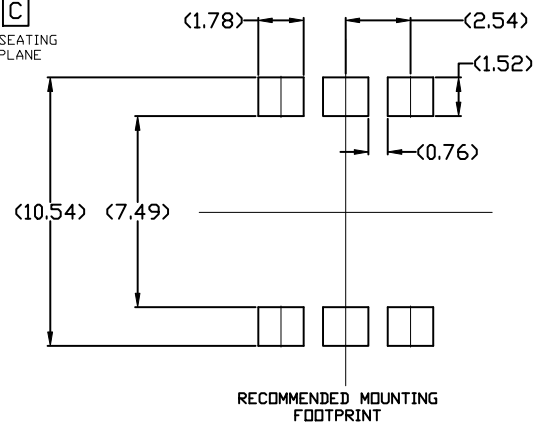
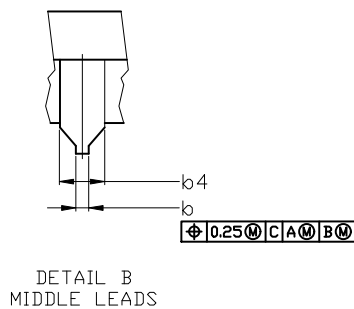
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2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS A, A1, AND L ARE MEASURED WITH THE PACKAGE SEATED.
4. DIMENSIONS D, D1, AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 2.54mm.
5. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).
6. CENTER LINE OF CORNER LEADS ARE LOCATED BY LOCATING THE CENTER OF FEATURE b2 AND b3.

| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | --- | --- | 4.80 |
| A1 | 0.38 | --- | --- |
| A2 | 3.28 | 3.40 | 3.53 |
| A3 | 2.49 REF | | |
| A4 | 1.89 REF | | |
| b | 0.41 | 0.46 | 0.51 |
| b1 | 0.76 | 0.92 | 1.14 |
| b2 | 0.25 | 0.28 | 0.36 |
| b3 | 1.02 | 1.40 | 1.78 |
| b4 | 1.778 REF | | |
| c | 0.20 | 0.25 | 0.30 |
| D | 8.13 | 8.51 | 8.89 |
| D1 | 0.86 REF | | |
| E | 6.10 | 6.35 | 6.60 |
| E1 | 8.43 | 9.17 | 9.90 |
| E2 | 8.13 REF | | |
| e | 2.54 BSC | | |
| L | 0.16 | 0.52 | 0.88 |



For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

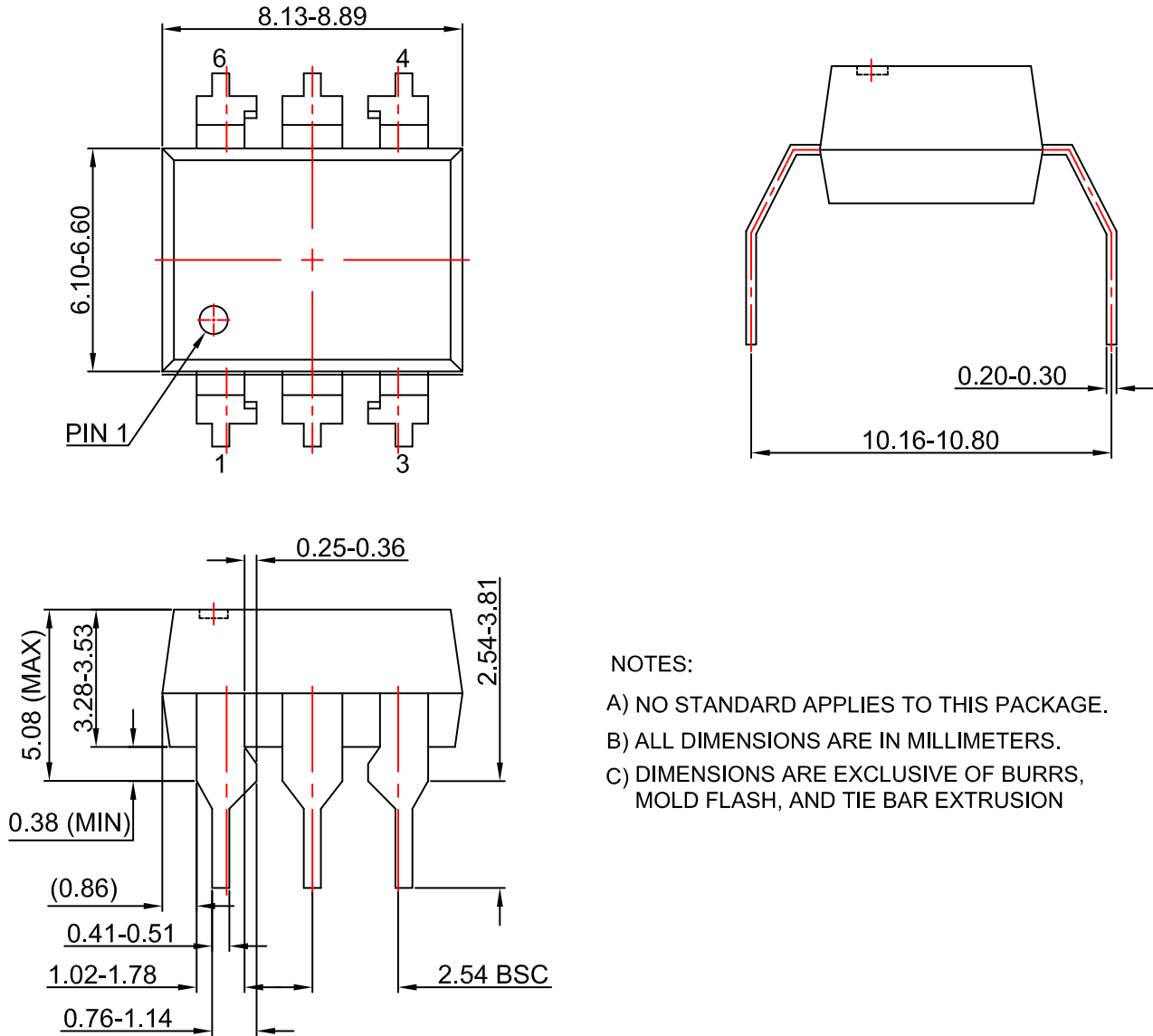
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